



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SC2383 TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 0.9 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 1 A

Collector-base voltage

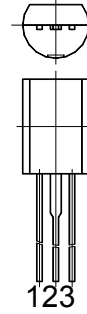
$V_{(BR)CBO}$: 160 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	160		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB} = 150\text{ V}, I_E = 0$		1	μA
Collector cut-off current	I_{CER}	$V_{CB} = 150\text{ V}, R_{EB} = 10M\Omega$		10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6V, I_C = 0$		1	μA
DC current gain	h_{FE}	$V_{CE} = 5\text{ V}, I_C = 200\text{ mA}$	60	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$		1	V
Base-emitter voltage	V_{BE}	$I_C = 5\text{ mA}, V_{CE} = 5V$		0.75	V
Transition frequency	f_T	$V_{CE} = 5\text{ V}, I_C = 200\text{ mA}$	20		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	60-120	100-200	160-320